T-03-09

T-07-19

Silicijeve planarne signalne diode
Silicon planar signal diodes

Tip/Type		U_{BR} 100 µA (V)	I_{FAV} ϑ_{amb} = 25 °C (mA)	U_F pri/at I_F ϑ_{amb} = 25 °C (V)	(mA)	I_R pri/at 25 °C (nA)	pri/at U_R (V)	C pri/at 1 MHz U_R = 0V (pF)	t_{rr} (ns)		Sl./Fig.
BA 511	1N4148	100	150	1.0	10	25	20	4	4^1	8^2	1
BA 513	1N4448	100	150	1.0	100	25	20	4	4^1	8^2	
BA 517	1N4150	70 1 µA	200	1.0	200	100	50	2,5	4^2	4^2	
BA 518	1N4151	75 5 µA	150	1.0	50	50	50	2	2^1	4^2	
BA 519	1N4152	40 5 µA	150	0.88	20	50	30	2	2^1	4^2	
BA 520	1N4153	75 5 µA	150	0.88	20	50	50	2	2^1	4^2	
BA 521	1N4154	35 5 µA	150	1.0	30	100	25	4	2^1	4^2	
BA 523	1N4444	70 5 µA	200	1.0	100	50	50	2	7^2	7^2	
BA 531	1N4727	30 5 µA	150	0.85	10	100	20	4	4^2	4^2	
BA 533	1N4864	125	200	1.1	100	100	80	1.3	4^1	8^2	
BA 543	BAY 17	15	200	1.0	100	100	12	1.5	50^3	50^2	
BA 544	BAV 18	60	200	1.0	100	100	50	1.5	50^3	50^2	
BA 545	BAV 19	120	200	1.0	100	100	100	1.5	50^3	50^2	
BA 546	BAY 20	180	200	1.0	100	100	150	1.5	50^3	50^2	
BA 547	BAY 80	150	200	1.0	100	100	120	6	50^3	50^2	

* pri/at 100° C

[1] $I_F = 10$ mA, $U_R = 6$ V, $i_{RR} = 1$ mA, $R_L = 100\ \Omega$

[2] $I_F = 10$ mA, $I_R = 10$ mA, $i_{RR} = 1$ mA

[3] $I_F = 30$ mA, $I_R = 30$ mA, $i_{RR} = 3$ mA, $R_L = 100\ \Omega$

Silicijeve preklopne didode
Silicon switching diodes

Tip/Type	U_{RRM} (V)	I_F (mA)	ϑ_{stg} (°C)	U_F pri/at I_F (V)	(mA)	C pri/at 1 MHz U_R = 3V (pF)	r_f pri/at f = 100 MHz I_F = 10 mA (Ω)	Sl./Fig.
BA 244 A	20	100	−50 do/to +100	<1	100	<1,8	0,5	1
BA 182 A	20	100	−40 do/to +100	<1,2	100	<1,25	0,7	2

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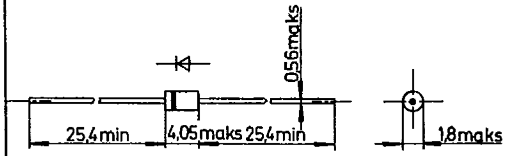
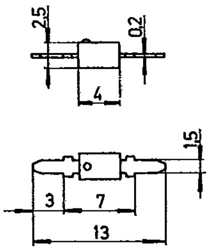
Capacitance diodes

Tip/Type	U_{RRM} (V)	C_r pri/at U_R (1 MHz) (pF)	(V)	$\frac{C_r(U_{R1})}{C_r(U_{R2})}$	U_{R1} (V)	U_{R2} (V)	r_s (Ω)	Sl./Fig.
BB 105 A	30	2,3 do/to 2,8	25	4 do/to 5	3	25	0,8	2
BB 105 B		2 do/to 2,3	25	4,5 do/to 6	3	25	0,8	
BB 105 G		1,8 do/to 2,8	25	4 do/to 6	3	25	1,2	



Sl./Fig. 1 **DO-35**



Sl./Fig. 2